Homework 2

NYCU EE 112511210 黃仲璿

Introduction to Library: CIC 0.18um 1.8V/3.3V 1P6M virtual Mixed Mode/RFCMOS Process

Availabe corners: (pmos-nmos)

- TT (typical typical)
- FF (fast fast)
- SS (slow slow)
- FS
- SF

Available MOS Models

- N_18 (1.8v nmos)
- N_BPW_18 (1.8v p-well nmos)
- P_18 (1.8v pmos)
- N_33 (3.3v nmos)
- N_BPW_33
- P_33
- N_LV_18 (low threshold voltage 1.8v nmos)
- P_LV_18
- N_LV_33
- P_LV_33
- N_ZERO_18 (zero Vt 1.8v nmos)
- N_ZERO_33

Design Rule

Library Summary

For homework simulation, use:

- TT type
- N_18 and P_18 for 1.8V nmos and pmos
- LMIN = 0.18u and WMIN = 0.25u
- assume minimal channel length/width delta = 0.01u
- assume temperature = 27 C

Problem 2-1-1

Initial Guess

Source Code

Simulation Result

```
element 0:mn1 0:mp1
model 0:n_18.1 0:p_18.1
region Saturati
id 45.7379u -10.5697u
...
```

We see that id of nmos is 4.5 times larger than target (10u), and id of pmos is very close to target (10u). Note:

$$I_D = \mu_n C_{ox} rac{W}{L} igg[(V_{GS} - V_{th}) V_{DS} - rac{V_{DS}^2}{2} igg]$$

pmos: fine-tune Lp up one step (0.01u) every time. nmos: change Ln to 4.5 times the original (0.81u), then perform fine-tuning.

NMOS Tuning

Source Code

```
* HW2_1_1_b.sp
.lib 'cic018.1' tt
.temp 27
.option post
*_____
* Simulation netlist
*_____
*nmos
Vg g gnd 0.9
Vd d gnd 0.9
Vdd ndd gnd 1.8
MN1 d g gnd gnd N_18 W=0.25u L=LN
*MP1 d g ndd ndd P_18 W=0.25u L=LP
*MN1 d g gnd gnd N_18 W=0.25u L=0.18u
*MP1 d g ndd ndd P_18 W=0.25u L=0.18u
*_____
* Stimulus
*_____
.dc Vdd 0 1.8 1.8 sweep LN 0.81u 1.0u 0.01u
*.dc Vg 0 0.9 0.9 sweep LP 0.18u 0.2u 0.01u
.probe i1(MN1)
*.probe i1(MP1)
.meas DC IMeas find i1(MN1) when v(g)=0.9
*.meas DC IMeas find i1(MP1) when v(g)=0.9
.end
```

Simulation Result:

when Ln parameter ln = 0.9u, id is closest to 10uA (1.0025E-05 A).

PMOS Tuning

Source Code: same as above except tune pmos

Simulation Result:

```
******

* hw2_1_1_b.sp

*** parameter lp = 180.0000n

imeas= -1.0570E-05

******

* hw2_1_1_b.sp

*** parameter lp = 190.0000n

imeas= -9.2225E-06

*******
```

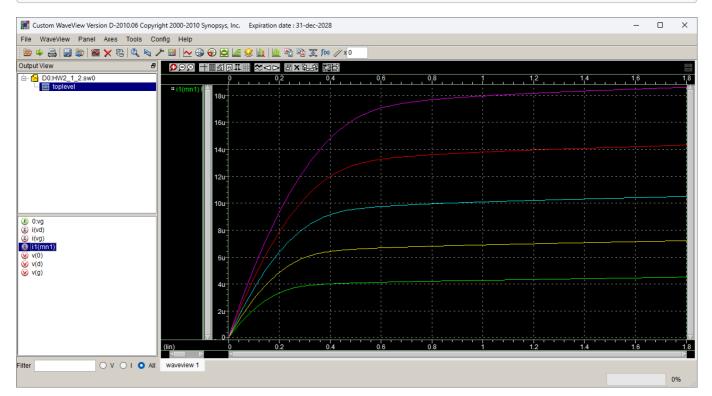
when Lp parameter 1p = 0.18u, id is closest to 10uA (-1.0570E-05 A)

Result

```
For nmos we choose Wn = 0.25u, Ln = 0.9u.
For pmos we choose Wp = 0.25u, Lp = 0.18u.
```

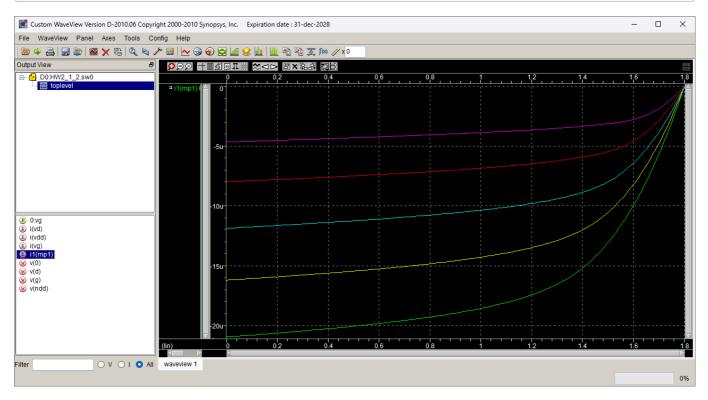
Problem 2-1-2

NMOS



PMOS

```
.dc Vd 0 1.8 0.01 sweep Vg 0.7 1.0 0.1
.probe i1(MP1)
```



Problem 2-2-1

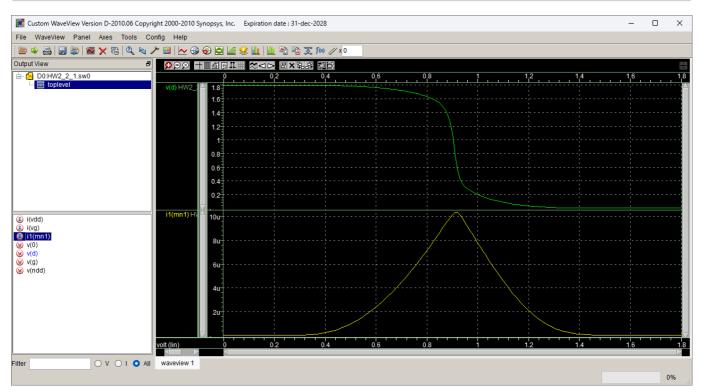
Parallel connecting M nmoses is the equivalent of multiplying Ln by M, thus multiplying Io. The same idea applies to pmos. Therefore, to have Io = 10uA, 20uA, 30uA, we use:

```
*Io = 10u
MN1 d g gnd gnd N_18 W=0.25u L= 0.9u M=1
MP1 d g ndd ndd P_18 W=0.25u L=0.18u M=1

*Io = 20u
MN1 d g gnd gnd N_18 W=0.25u L= 0.9u M=2
MP1 d g ndd ndd P_18 W=0.25u L=0.18u M=2

*Io = 30u
MN1 d g gnd gnd N_18 W=0.25u L= 0.9u M=3
MP1 d g ndd ndd P_18 W=0.25u L=0.18u M=3
```

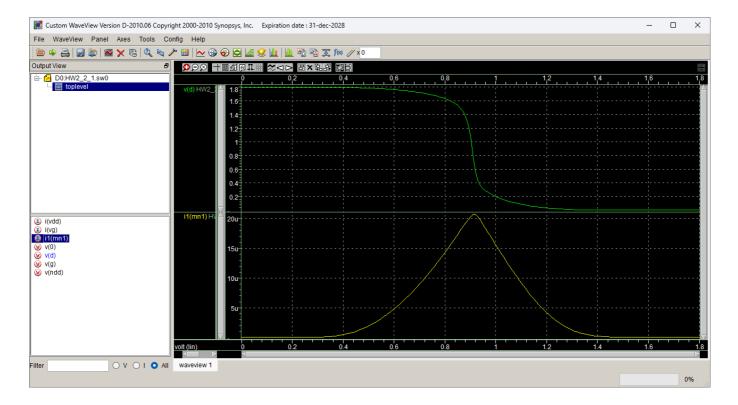
lo = 10uA (M = 1)



lo = 20uA (M = 2)

Code same as above, except

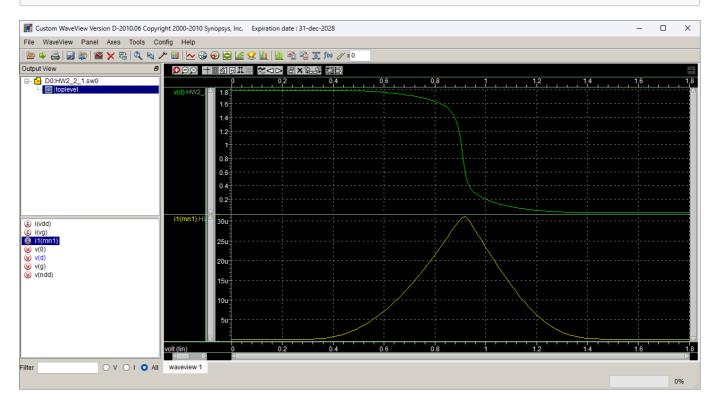
MN1 d g gnd gnd N_18 W=0.25u L=0.90u M=2 MP1 d g ndd ndd P_18 W=0.25u L=0.18u M=2



lo = 30uA (M = 3)

Code same as above, except

MN1 d g gnd gnd N_18 W=0.25u L=0.90u M=3 MP1 d g ndd ndd P_18 W=0.25u L=0.18u M=3



V1 = 0.7V

Initial Guess

Source Code: same as Problem 2-1-1 except set all Vg to 0.7

Simulation Result:

```
element 0:mn1 0:mp1
model 0:n_18.1 0:p_18.1
region Saturati
id 21.5095u -18.9496u
```

We see that id of both nmos and pmos are very close to target (20u).

- pmos: to increase current, fine-tune Wp up one step (0.01u) every time.
- nmos: to decrease current, fine-tune Ln up one step (0.01u) every time.

NMOS

Simulation Result:

```
* hw2_2_2_07.sp

*** parameter ln = 180.0000n

imeas= 2.1509E-05

*****

* hw2_2_2_07.sp

*** parameter ln = 190.0000n

imeas= 1.9373E-05

...
```

when Ln parameter ln = 0.19u, id is closest to 20uA (1.9373E-05 A)

PMOS

Simulation Result:

```
*** hw2_2_2_07.sp

*** parameter wp = 260.0000n

1.80000    -19.9722u

******

* hw2_2_2_07.sp

*** parameter wp = 270.0000n

1.80000    -20.9425u

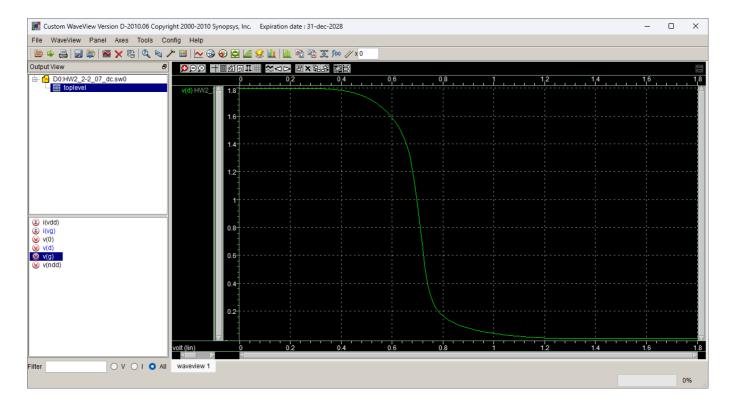
***
```

when Wp parameter wp = 0.26u, id is closest to 20uA (-19.9722u A)

Result

```
nmos W = 0.25u L = 0.19u
pmos W = 0.26u L = 0.18u
```

```
* HW2_2_2_07_dc.sp
.lib 'cic018.1' tt
.temp 27
.option post
*_____
* Simulation netlist
*_____
Vg g gnd
*Vd d gnd 0.9
Vdd ndd gnd 1.8
MN1 d g gnd gnd N_18 W=0.25u L=0.19u
MP1 d g ndd ndd P_18 W=0.26u L=0.18u
* Stimulus
.dc Vg 0 1.8 0.01
.op
.end
```



Vg = 0.8

Initial Guess

Source Code: same as Problem 2-1-1 except set all Vg to 0.8

Simulation Result:

```
element 0:mn1 0:mp1
model 0:n_18.1 0:p_18.1
region Saturati
id 33.1641u -14.5751u
```

We see that id of both nmos and pmos are very close to target (20u).

- pmos: to increase current, fine-tune Wp up one step (0.01u) every time.
- nmos: to decrease current, multiply Ln by 1.2 (0.22u), then fine-tune Ln up one step (0.01u) every time.

NMOS

when Ln parameter ln = 0.29u, id is closest to 20uA (2.0368E-05 A)

PMOS

when Wp parameter wp = 0.33u, id is closest to 20uA (-19.9570u A)

Result

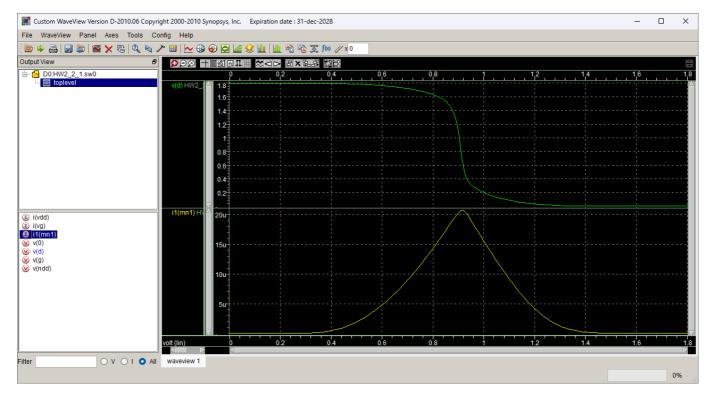
```
nmos W = 0.25u L = 0.29u
pmos W = 0.33u L = 0.18u
```

```
* HW2_2_2_08_dc.sp
*_____
.lib 'cic018.1' tt
.temp 27
.option post
*_____
* Simulation netlist
Vg g gnd
*Vd d gnd 0.9
Vdd ndd gnd 1.8
MN1 d g gnd gnd N 18 W=0.25u L=0.29u
MP1 d g ndd ndd P_18 W=0.33u L=0.18u
*_____
.dc Vg 0 1.8 0.01
.op
.end
```

![image./pic7.png)

Vg = 0.9

```
Same as Problem 2-2-1 nmos W = 0.25u L = 0.90u M = 2
pmos W = 0.25u L = 0.18u M = 2
```



Vg = 1.0

Initial Guess

Source Code: same as Problem 2-1-1 except set all Vg to 1.0

Simulation Result:

```
element 0:mn1 0:mp1
model 0:n_18.1 0:p_18.1
region Saturati
id 60.0367u -6.8436u
```

We see that id of nmos is roughly 3 times larger than the target (20uA), and pmos is roughly third of such.

- pmos: to increase current, multiply Wp by 2 (0.50u), fine-tune Wp up one step (0.01u) every time.
- nmos: to decrease current, multiply Ln by 3 (0.75u), then fine-tune Ln up one step (0.01u) every time.

NMOS

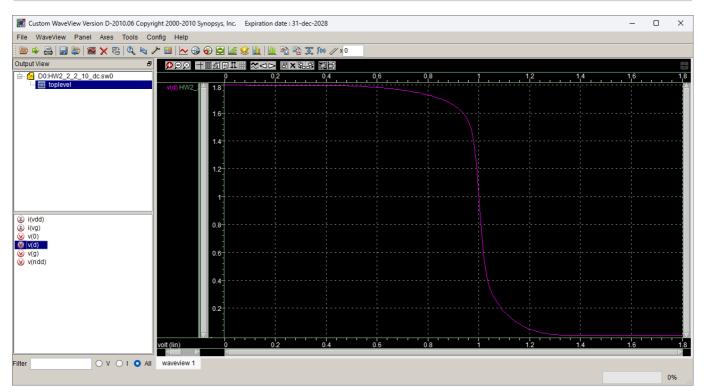
when Ln parameter ln = 0.58u, id is closest to 20uA (19.9363u A)

PMOS

when Wp parameter wp = 0.80u, id is closest to 20uA (-20.0495u A)

Result

```
nmos W = 0.25u L = 0.58u
pmos W = 0.80u L = 0.18u
```



Vg = 1.1

Initial Guess

Source Code: same as Problem 2-1-1 except set all Vg to 1.1

Simulation Result:

```
element 0:mn1 0:mp1
model 0:n_18.1 0:p_18.1
```

```
region Saturati
id 73.6641u -3.8705u
```

We see that id of nmos is roughly 3.5 times larger than the target (20uA), and pmos is roughly sixth of such.

- pmos: to increase current, multiply Wp by 5 (1.25), fine-tune Wp up one step (0.01u) every time.
- nmos: to decrease current, multiply Ln by 6 (0.84u), then fine-tune Ln up one step (0.01u) every time.

NMOS

when Ln parameter ln = 0.79u, id is closest to 20uA (20.0234u A)

PMOS

```
* hw2_2_2_11.sp

*** parameter wp = 1.6100u ***

1.80000 -19.9563u

******

* hw2_2_2_11.sp

*** parameter wp = 1.6200u ***

1.80000 -20.0835u
```

when Wp parameter wp = 1.61u, id is closest to 20uA (-19.9563u A)

Result

```
nmos W = 0.25u L = 0.79u
pmos W = 1.61u L = 0.18u
```

